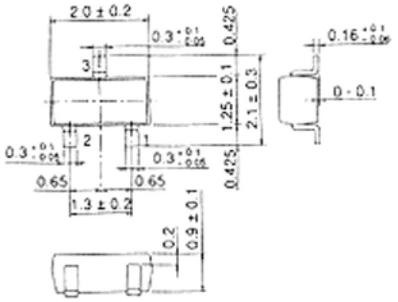
HITACHI

2SC4265

SILICON NPN EPITAXIAL

VHF RF AMPLIFIER, LOCAL OSCILLATOR, MIXER



1. Emitter
2. Base
3. Collector

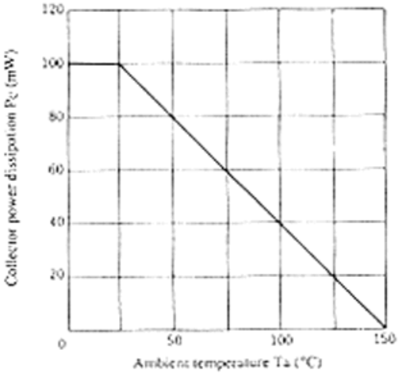
(Dimensions in mm)

(CMPAK)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC4265	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	50	mA
Collector power dissipation	P_C	100	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu A$, $I_E = 0$	30	—	—	V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1mA$, $R_{BE} = \infty$	20	—	—	V
Collector cutoff current	I_{CBO}	$V_{CE} = 15V$, $I_E = 0$	—	—	0.5	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 3V$, $I_C = 0$	—	—	10	μA
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 20mA$, $I_B = 4mA$	—	—	1.0	V
DC current transfer ratio	h_{FE}	$V_{CE} = 10V$, $I_C = 10mA$	40	—	—	
Collector output capacitance	C_{ob}	$V_{CB} = 10V$, $I_E = 0$, $f = 1MHz$	—	—	1.5	pF
Gain bandwidth product	f_T	$V_{CE} = 10V$, $I_C = 10mA$	600	—	—	MHz

• Marking is [IC].

■ See characteristic curves of 2SC2735.